

MJ P-Channel Enhancement Mode Power MOSFET

Description

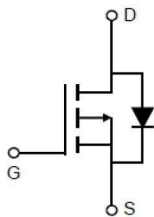
The MJ60P05N uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for use as a load switch or in PWM applications.

General Features

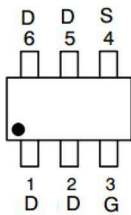
- ◆ $V_{DS}=-60V, I_D=-5A$
 $R_{DS(ON)}<65m\Omega @ V_{GS}=-10V$
 $R_{DS(ON)}<85m\Omega @ V_{GS}=-4.5V$
- ◆ High density cell design for ultra low R_{dson}
- ◆ Fully characterized avalanche voltage and current
- ◆ Excellent package for good heat dissipation

Application

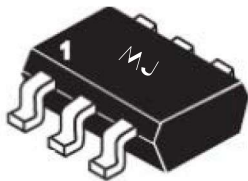
- ◆ Load switch
- ◆ PWM application



Schematic diagram



Marking and pin assignment



SOT23-6L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJ60P05N	MJ60P05N	SOT-23-6L	Ø 180mm	8 mm	3000 units

Absolute Maximum Ratings (T_c =25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-5	A
Pulsed Drain Current	I_{DM}	-20	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	40.3	°C/W
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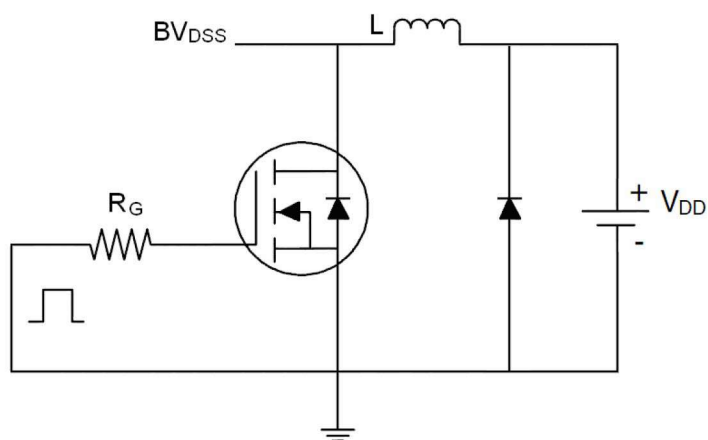
Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =±20V,V _{GS} =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5A	-	55	65	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	70	85	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-5A	-	10	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C _{iss}	V _{DS} =-30V,V _{GS} =0V F=1.0MHz	-	1153	-	PF
Output Capacitance	C _{oss}		-	93.7	-	PF
Reverse Transfer Capacitance	C _{rss}		-	77.7	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V,R _L =6Ω V _{GS} =-10V,R _G =3Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	32	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q _g	V _{DS} =-30V,I _D =-5A V _{GS} =-10V	-	15.8	-	nC
Gate-Source Charge	Q _{gs}		-	2.7	-	nC
Gate-Drain Charge	Q _{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V _{SD}	V _{GS} =0V,I _S =-5A	-	-	-1.2	V
Diode Forward Current <small>(Note 2)</small>	I _S		-	-	-5	A
Reverse Recovery Time	t _{rr}	T _J =25°C, I _F =-5A di/dt=-100A/μs <small>(Note 3)</small>	-	27	-	nS
Reverse Recovery Charge	Q _{rr}		-	32	-	nC

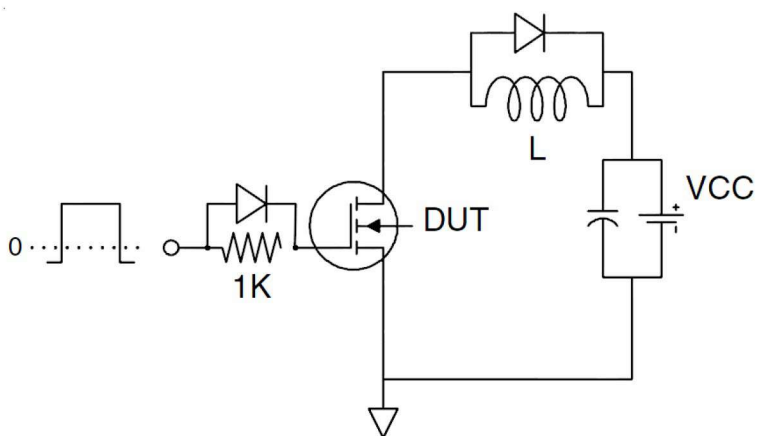
Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t≤10sec.
③ Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.
④ Guaranteed by design, not subject to production

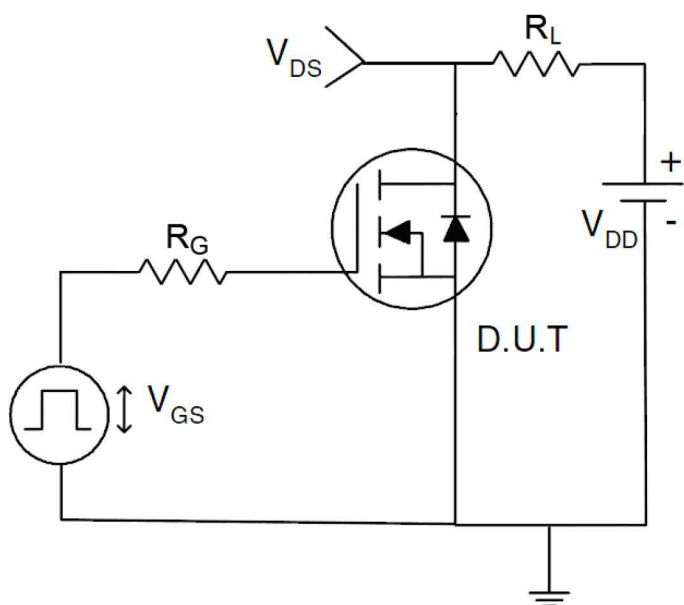
Test Circuit



EAS test Circuit

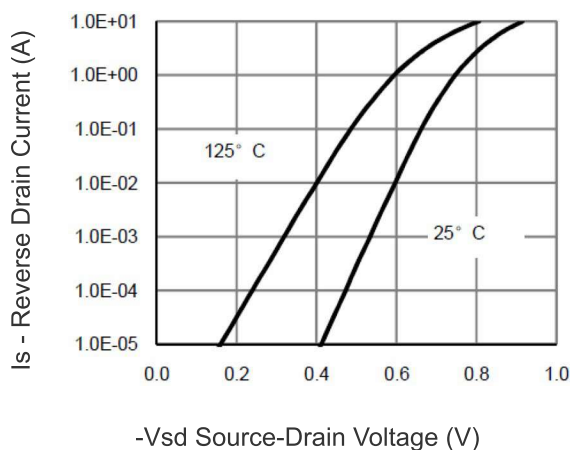
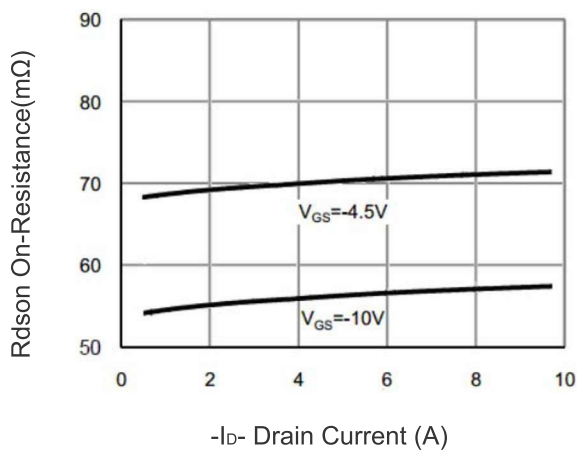
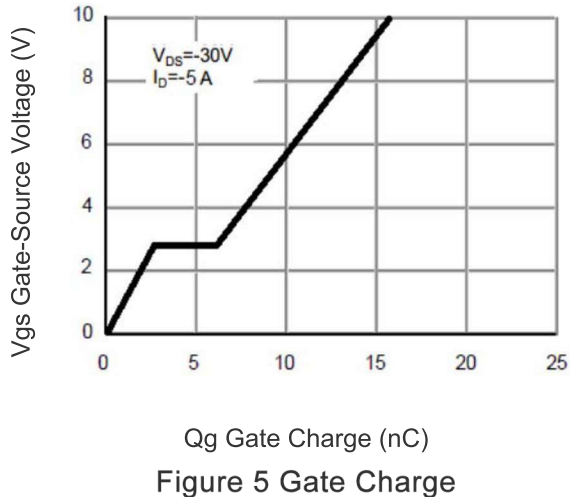
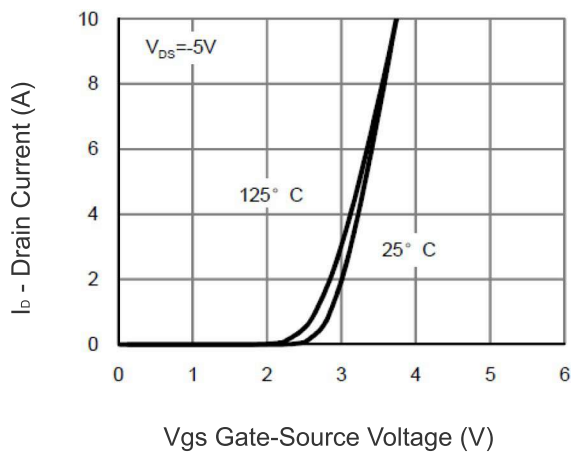
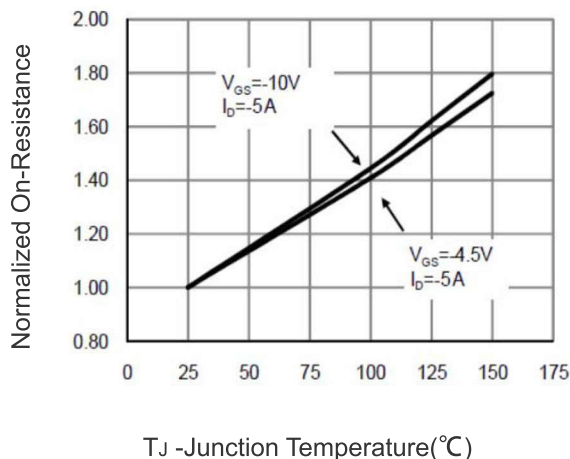
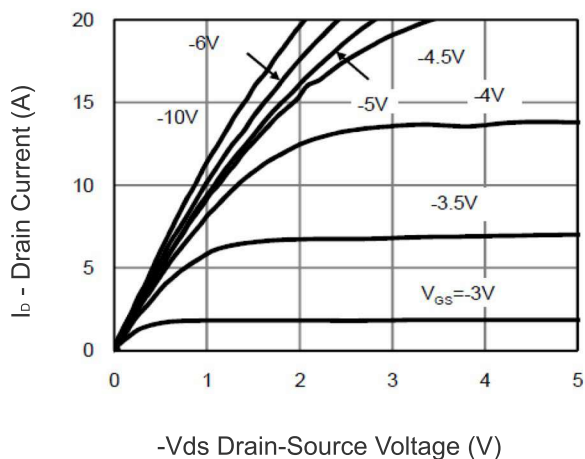


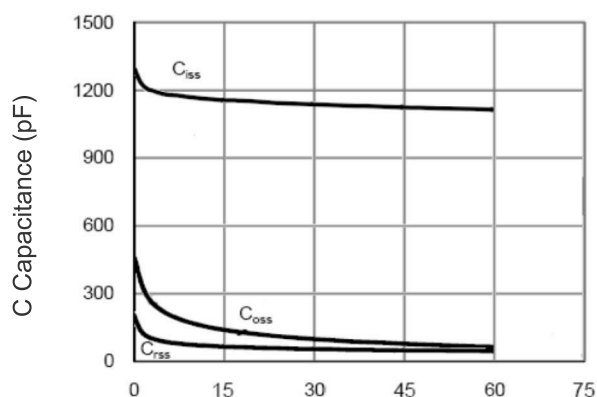
Gate charge test Circuit



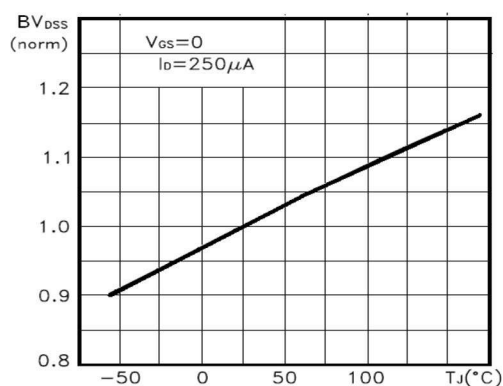
Switch Time Test Circuit

Typical Electrical and Thermal Characteristics

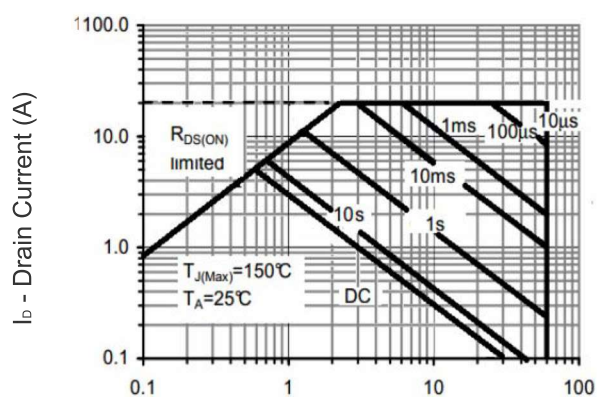




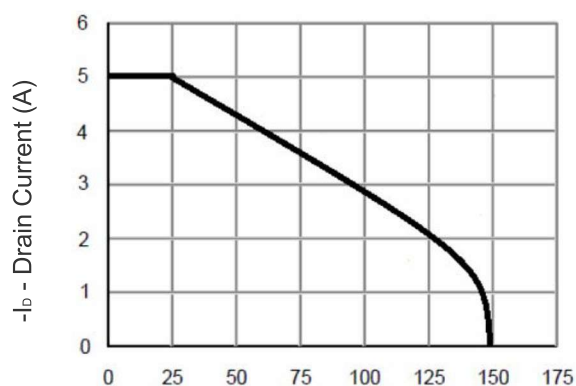
-Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



TJ -Junction Temperature(°C)
Figure 9 BV_{DSS} vs Junction Temperature



-Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ -Junction Temperature(°C)
Figure 10 Id Current De-rating

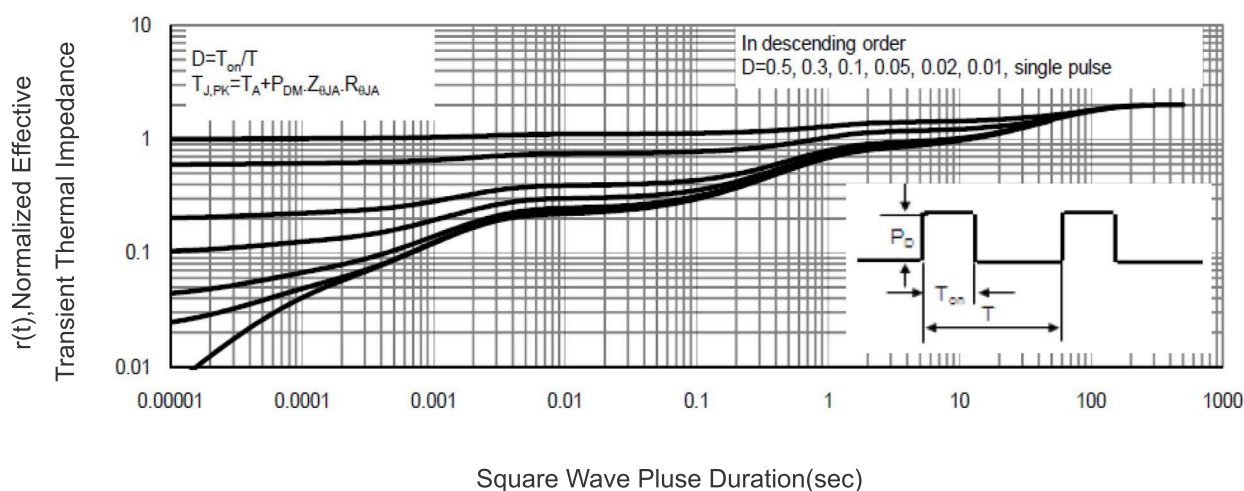
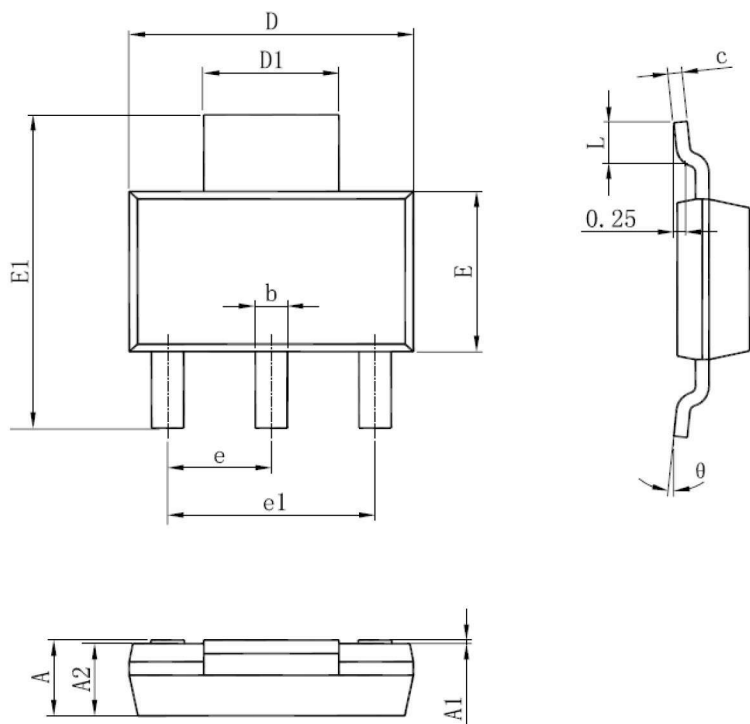


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-223 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

Notes:

- ① All dimensions are in millimeters.
- ② Tolerance ±0.10mm (4 mil) unless otherwise specified
- ③ Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- ④ Dimension L is measured in gauge plane.
- ⑤ Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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